

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#3A
NEAL

In re the Application of

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YAMAGUCHI

Application No.: U. S. National Stage
of PCT/JP00/02850

Filed: January 18, 2001

Docket No.: 108360

For: SILICON SINGLE CRYSTAL AND WAFER DOPED WITH GALLIUM AND
METHOD FOR PRODUCING THEM

PRELIMINARY AMENDMENT

Director of the U.S. Patent and Trademark Office
Washington, D. C. 20231

Sir:

Prior to initial examination, please amend the above-identified application as follows:

IN THE CLAIMS:

✓ Please cancel claims 1-19 without prejudice to or disclaimer of the subject matter

contained therein. Please add new claims 20-42 as follows: